

PTO-1449 Information Disclosure Citation in an Application		Application No.		Applicant(s): Hans Norström et al.			
		Docket Number 068758.0182		Group Art Unit		Filing Date April 21, 2004	

U.S. PATENT DOCUMENTS							
		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>~</i>	1	5,587,327	12-24-96	König et al.	437	31	05-23-95
<i>~</i>	2	5,821,149	10-13-98	Schüppen et al.	438	312	03-14-97
<i>~</i>	3	6,251,738	06-26-01	Huang	438	312	01-10-00

FOREIGN PATENT DOCUMENTS								
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<i>translation is required!</i>	4	DE 196 52 423 A1	06-10-98	GERMANY	H01L	29/737		x
<i>~</i>	5	SE 0101567-6	12-23-02	SWEDEN	H01L	21/8249	x	
<i>~</i>	6	EP 1 139 408 A2	01-26-01	EPO	H01L	21/331	x	
<i>~</i>	7	WO 98/53489	11-26-98	PCT	H01L	21/331	x	
<i>~</i>	8	WO 01/20664	03-22-01	PCT	H01L	21/76	x	

NON-PATENT DOCUMENTS		
	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)	DATE
<i>~</i>	9 A Schüppen et al., "Enhanced SiGe Heterojunction Bipolar Transistors with 160 GHz- f_{max} "; IEEE IEDM Tech Dig., p. 743	1995
<i>~</i>	10 A. Monroy et al., "BiCMOS6G: A high performance .035 μ m SiGe BiCMOS technology for wireless applications", IEEE BCTM, p. 121	1999
<i>~</i>	11 S.A. St. Onge et al., "A 0.24 μ m SiGe BiCMOS Mixed-Signal RF Production Technology Featuring a 47 GHz f_t HBT and 0.18 μ m L_{eff} CMOS", IEEE BCTM99, p. 117	1999
<i>~</i>	12 John D. Cressler, "SiGe HBT Technology: A New Contender for Si-Based RF and Microwave Circuit Applications"; IEEE Transactions on Microwave Theory and Techniques, Vol. 46, No. 5	May 1998
<i>~</i>	13 D. Behammer, et al.; "Si/SiGe HBTs for Application in Low Power ICs"; Solid-State Electronics, Vol. 39, No. 4, pp. 471-480	1996

EXAMINER <div style="text-align: center;"><i>[Signature]</i></div>	DATE CONSIDERED <div style="text-align: center;"><i>8/26/05</i></div>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.